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Charge pumping through the interface between topological insulator with massive surface Dirac fermions and a precessing ferromagnet

Farzad Mahfouzi,[1] Naoto Nagaosa,[2,3] and Branislav K. Nikolić[1,2]

[1]*Department of Physics and Astronomy, University of Delaware, Newark, DE 19716-2570, USA*
[2]*Cross-Correlated Materials Research Group (CMRG) and Correlated Electron Research Group (CERG), RIKEN-ASI, Wako, Saitama 351-0198, Japan*
[3]*Department of Applied Physics, University of Tokyo, Tokyo 113-8656, Japan*

We study charge pumping through the interface between the ferromagnetic (F) overlayer and a three-dimensional topological insulator (TI) using multiphoton nonequilibrium Green function formalism. The microwave-driven magnetization precession of the F overlayer leads to the time-dependent exchange field which can induce surface energy gap via the magnetic proximity effect, thereby forcing Dirac fermions on the TI surface to acquire a time-dependent mass. This leads to the huge enhancement of the dc pumping voltage $V_{\rm pump}$, which is proportional to the microwave frequency ω, when compared with the case without the surface gap opening where $V_{\rm pump}$ is governed only by the spin-orbit coupling on the surface of TI. The predicted effect survives even when the Fermi energy is outside of the surface gap or with finite density of charge carriers in the bulk of the TI slab.

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The recent experimental discovery [1–3] of three-dimensional (3D) topological insulators (TIs), which posses a usual bandgap in the bulk while supporting exotic metallic states on their surfaces, has opened new avenues to explore low energy quantum phenomena in two-dimensional condensed matter systems, as well as bench-top setting to create particles (such as axions, monopoles and Majorana fermions [2]) conjectured in high energy physics. The strong spin-orbit coupling (SOC), as the key ingredient in this novel materials, causes spin-momentum locking of low-energy quasiparticles described by a *single* Dirac cone on the TI surface which is not seen in related systems, such as two-dimensional electron gases (2DEGs) [4] or graphene [5] with the Rashba SOC.

Since helical surface states of 3D TIs are gapless, they respond *strongly* to any time-reversal symmetry breaking perturbations such as covering the surface by magnetic impurities [6] or a ferromagnetic (F) overlayer [7]. In such situation, the Dirac cone is perturbed by the proximity induced exchange coupling which leads to a surface energy gap $\Delta_{\rm surf}$ at the Dirac point observed in recent experiments [6]. The corresponding massive Dirac fermions exhibit half-quantized Hall conductivity, $\sigma_H = \pm e^2/2h$, even in the limit of vanishingly small $\Delta_{\rm surf} \to 0$, as long as the Fermi energy lies within the surface gap $\Delta_{\rm surf}$ in clean samples [2] (or within the bulk gap in TI samples where magnetic disorder localizes surface quantum states [8]). This effect, known in high energy physics as parity anomaly, is determined by the bulk topology and, therefore, serves to *distinguish* TI surface states from all other 2D systems or topologically trivial surfaces in condensed matter physics [2].

However, unlike the well-known integer quantum Hall effect, where chiral edge states carry current and connect to external leads in multiterminal Hall bars, σ_H on the surface of TI *cannot be measured* by conventional multiterminal dc transport setups since either edge states do not exist (if the whole surface of TI is covered by magnetic impurities) or one finds the usual $\sigma_H = e^2/h$ when chiral gapless edge state propagates along the domain wall if only portion of the TI surface is covered by magnetic impurities [2]. Thus, experimental efforts to detect manifestations of gapped helical surface states of 3D TI have been directed toward magnetoelectric effects probed using electromagnetic (EM) radiation in order to measure magneto-optical Kerr $\theta_{\rm K}$ and Faraday $\theta_{\rm F}$ rotation angles

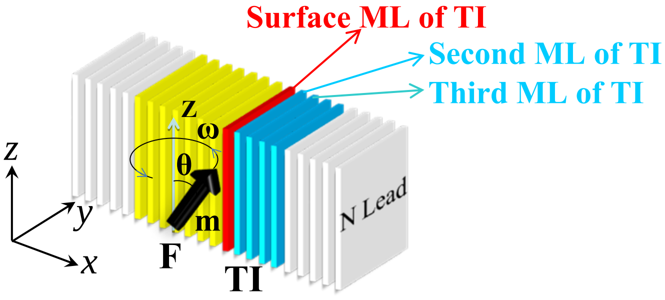

FIG. 1: (Color online) Schematic view of the topological insulator-based semi-MTJ which pumps charge current $\propto \omega$ along the x-axis due to magnetization dynamics driven by the absorption of microwaves of frequency ω under the FMR conditions. The semi-MTJ contains a single F layer of finite thickness whose magnetization $\mathbf{m}(t)$ is precessing around the z-axis. The precessing F layer is attached to the left semi-infinite N lead and to 3D TI slab on the right, so that as soon as the precession cone angle θ becomes finite energy gap $\Delta_{\rm surf}(t)$ can appear on the surface of TI due to proximity effect governed by the component of the magnetization perpendicular to the F|TI interface. Each layer is composed of monolayers (MLs) modeled on an infinite square tight-binding lattice. No dc bias voltage is applied between the N leads.

for EM wave propagating through a slab of TI that is weakly exchange-coupled to F layer [9–11]. Demonstrating that for TI slabs thinner than the radiation wavelength $\theta_{\rm F}$ is quantized in units of the fine structure constant while $\theta_{\rm K} = -90^\circ$ would confirm the topological property of the bulk [11]. However, these experiments require negligible bulk conductivity—otherwise the universality of $\theta_{\rm F}$ and $\theta_{\rm K}$ values is broken [11]. This is difficult to achieve in presently available TI samples which are always unintentionally doped (e.g., $\rm Bi_2Si_3$ is n-doped by the Se vacancies), thereby obscuring [12] topological properties anticipated for perfectly insulating bulk [2].

In this Letter, we predict a novel charge pumping phenomenon in vertical F|TI multilayers in the *absence* of any dc bias voltage which is *very sensitive* to the presence or absence of the surface gap $\Delta_{\rm surf}$ and, therefore, can be employed to detect the presence of massive Dirac fermions by measuring the dc pumping voltage. Our device setup is illustrated in Fig. 1 where finite thickness F layer in contact with finite thickness TI slab are sandwiched between two normal metal (N) leads to form a semi-magnetic tunnel junction (MTJ). The dynamics of the magnetization of F layer as coherent macrospin precession is induced by the absorption of microwaves under the conditions of ferromagnetic resonance (FMR). Such FMR situation in conventional ferromagnetic multilayers leads to pumping of pure spin current by the F|N *interfaces*, which has been amply explored over the past decade as a robust and ubiquitous effect at room temperature [13].

On the other hand, using recently developed [14] nonequilibrium Green function (NEGF) theory of spin pumping in the presence of strong interfacial SOC, we demonstrate in Fig. 2(a) and (b) that proposed device in Fig. 1 would pump time-dependent charge current $I(t)$, proportional to the microwave frequency ω, in the direction perpendicular to the interface F|TI. As soon as the cone angle θ becomes non-zero due to microwave absorption, the time-dependent exchange field acquires a component $(\Delta \sin\theta \sin\omega t)\mathbf{e}_x$ which is perpendicular to the surface of the TI and can induce the corresponding surface gap $\Delta_{\rm surf}(t)$. Note that the value of $\Delta_{\rm surf}^{\rm max}$ is not directly related to $\Delta|\sin\theta|$ since magnetic proximity effect can be influenced by the properties of the F|TI interface (discussed below in relation to Fig. 3).

The detection of parity anomaly on the (non-localized [8]) surface of TI requires to measure a physical quantity which experiences a *sudden jump* in its value at arbitrary small $\Delta_{\rm surf}$ and for the Fermi energy within the surface gap $|E_F - E_{\rm DP}| < \Delta_{\rm surf}$ ($E_{\rm DP}$ is the energy of the Dirac point). Although we do not see such discontinuity in the setup of Fig. 1, we do find in Fig. 2(a) that dc pumping voltage in an open circuit $V_{\rm pump} = I/G(\theta)$ is about *three orders of magnitude* larger at small cone angles θ if $\Delta_{\rm surf}^{\rm max} \neq 0$ when compared to the junction with $\Delta_{\rm surf} \equiv 0$. Here I is the time-averaged value of $I(t)$ in the N leads, and $G(\theta)$ is the conductance of F|TI|N semi-MTJ computed by tilting the *static* magnetization of the F layer by an angle θ away from the z-axis and by applying the linear-response bias voltage between the N leads. The precession cone angle can be controlled experimentally via the input microwave power in the typical range $\theta < 30^\circ$ [15], and F|TI heterostructures have already been fabricated [7], so that confirmation of the result in Fig. 2 is within the reach of present experimental technologies. Figures 2(b) and 2(d) shows that the signal $V_{\rm pump}(\Delta_{\rm surf}^{\rm max} \neq 0)$ remains larger than $V_{\rm pump}(\Delta_{\rm surf} \equiv 0)$ even when $|E_F - E_{\rm DP}| > \Delta_{\rm surf}^{\rm max}$, but pumping voltage in this case for the experimentally relevant range $\theta < 30^\circ$ is much smaller than in the opposite case [except very close to $E_{\rm DP}$ where it vanishes in Fig. 2(d)].

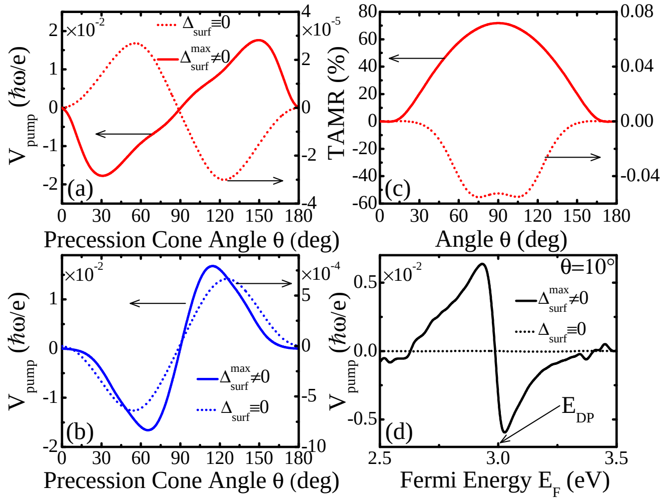

FIG. 2: (Color online) The dc pumping voltage in F|TI|N junction in Fig. 1 without $\Delta_{\rm surf} \equiv 0$ and with $\Delta_{\rm surf}^{\rm max} = 0.2|\sin\theta|$ eV energy gap on the surface of TI when Fermi energy is: (a) inside the surface gap $E_F - E_{\rm DP} = 0.01$ eV (for $\theta > 6^\circ$); or (b) outside of the surface gap $E_F - E_{\rm DP} = 0.35$ eV for all θ. Panel (c) shows tunneling anisotropic magnetoresistance (TAMR) corresponding to situation in panel (a), while panel (d) plots dc pumping voltage as a function of the Fermi energy for precession cone angle $\theta = 10^\circ$.

The non-zero pumping voltage at the adiabatic level $\propto \omega$ in junctions with interfacial SOC [14] (in the absence of interfacial SOC, simple F|I|N junctions pump [16] charge current $\propto \omega^2$ which is, therefore, nonadiabatic) is closely related to the tunneling anisotropic magnetoresistance (TAMR). The out-of-plane TAMR for F|TI|N semi-MTJ is defined [14] as TAMR $(\theta) = [R(90^\circ - \theta) - R(\theta = 90^\circ)]/R(\theta = 90^\circ)$ using conventional resistances measured by tilting the static magnetization of the F layer in Fig. 1 away from the transport direction $\theta = 90^\circ$. The TAMR curves plotted in Fig. 2(c) show that change in the conductance $G(\theta) = 1/R(\theta)$ is too small to account for the enormous difference between $V_{\rm pump}(\Delta_{\rm surf}^{\rm max} \neq 0)$ and $V_{\rm pump}(\Delta_{\rm surf}^{\rm max} \equiv 0)$ cases. Although TAMR differenti-

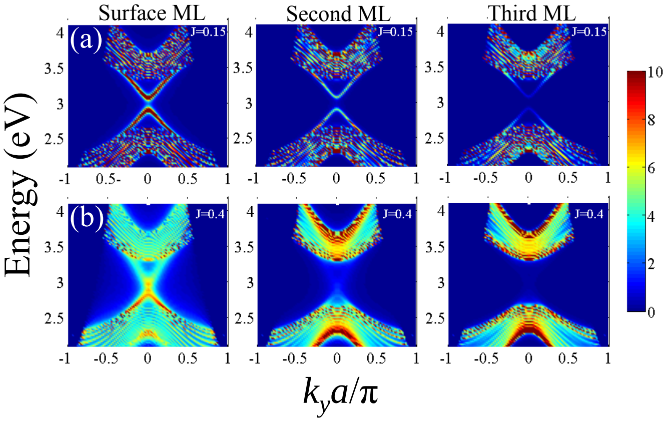

FIG. 3: (Color online) The local density of states $N(E, k_y, k_z = 0)$ on the surface of TI slab of thickness $d_F = 10$ MLs, as well as on the second and third ML marked in Fig. 1, which is either (a) weakly ($\gamma_c = 0.15$ eV) or (b) strongly ($\gamma_c = 0.4$ eV) coupled to the neighboring F overlayer of thickness $d_F = 50$ MLs. The F overlayer with magnetization perpendicular to the F|TI interface is assumed to induce surface gap $\Delta_{\rm surf}$ in the helical state of TI via the magnetic proximity effect.

ates between massless and massive Dirac fermions on the surface of the TI, it cannot be used to reliably detect the latter since it would diminish if bulk charge carriers are present within the TI slab.

In the EM radiation detection schemes, the TI slab which is semi-infinite is described by topological field theory (TFT) [2], or alternatively one considers TI slab of finite thickness with its bulk and surface conductivities [11]. The latter includes both the longitudinal and transverse (Hall) contributions [11] where the role of $(\alpha\Theta/4\pi^2)\mathbf{E}\cdot\mathbf{B}$ term ($\mathbf{E}$ and $\mathbf{B}$ are electromagnetic fields and α is the fine structure constant) in TFT is completely replaced by the appearance of explicit surface Hall conductivities (quantized or non-quantized) that influence the boundary conditions for EM wave propagating perpendicularly through the slab [11]. Our device in Fig. 1 for measuring currents and voltages is analogous to this viewpoint where the presence of TI surface, with strong SOC and possibly opening of $\Delta_{\rm surf}$ gap, in contact with the precessing F layer rectifies pumped spin current into charge current. The major advantage of our device is that due to perpendicular-to-plane transport geometry it can operate even if there are bulk charge carriers in the interior of the TI slab.

We now explain details of our formalism to obtain pumped charge current and corresponding $V_{\rm pump}$. The semi-MTJ in Fig. 1 is modeled on a simple cubic lattice where monolayers (MLs) of different materials (N, F, TI) are assumed to be infinite in the transverse yz-direction. The TI slab has thickness $d_{\rm TI} = 5$ MLs and the F layer has thickness $d_{\rm F} = 50$ MLs. The F and N layer are described by a tight-binding Hamiltonian with a single s-orbital per site

$$\hat{H}^{\rm F}_{\mathbf{k}_\|} = \sum_{n,\sigma\sigma',\mathbf{k}_\|} \hat{c}^\dagger_{n\sigma,\mathbf{k}_\|}\left(\varepsilon_{n,\mathbf{k}_\|}\delta_{\sigma\sigma'} - \frac{\Delta_n}{2}\mathbf{m}(t)\cdot[\hat{\boldsymbol{\sigma}}]_{\sigma\sigma'}\right)\hat{c}_{n\sigma',\mathbf{k}_\|} - \gamma\sum_{n,\sigma,\mathbf{k}_\|}(\hat{c}^\dagger_{n\sigma,\mathbf{k}_\|}\hat{c}_{n+1,\sigma,\mathbf{k}_\|} + \text{H.c.}). \qquad (1)$$

The operators $\hat{c}^\dagger_{\mathbf{n}\sigma}$ ($\hat{c}_{\mathbf{n}\sigma}$) create (annihilate) electron with spin σ on ML n with transverse momentum $\mathbf{k}_\|$ within the ML. The in-plane kinetic energy is $\varepsilon_{n,\mathbf{k}_\|} = -2\gamma(\cos k_y a + \cos k_z a)$, whose effect is equivalent to an increase in the on-site energy, and the inter-layer hopping is $\gamma = 1.0$ eV. The coupling of itinerant electrons to collective magnetization dynamics is described through the material-dependent exchange potential $\Delta_n = 0.2$ eV ($\Delta_n \equiv 0$ within semi-infinite ideal N leads), where $\hat{\boldsymbol{\sigma}} = (\hat{\sigma}_x, \hat{\sigma}_y, \hat{\sigma}_z)$ is the vector of the Pauli matrices and $[\hat{\sigma}_\alpha]_{\sigma\sigma'}$ denotes the Pauli matrix elements. The Hamiltonian in Eq. (1) is time-dependent since the unit vector $\mathbf{m}(t)$ along the local magnetization direction within the F layer, which is assumed to be spatially uniform, is steadily precessing around the z-axis with a constant cone angle θ as illustrated in Fig. 1.

The minimal model for the slab of 3D TI, such as Bi$_2$Se$_3$, is the effective tight-binding Hamiltonian with four orbitals per site [17]:

$$\hat{H}^{\rm TI}_{\mathbf{k}_\|} = \sum_{n,\mathbf{k}_\|}\left\{\mathbf{c}^\dagger_{n,\mathbf{k}_\|}\left(\frac{B}{a^2}\boldsymbol{\Gamma}_0 - \frac{iA}{2a}\boldsymbol{\Gamma}_3\right)\mathbf{c}_{n+1,\mathbf{k}_\|} + \text{H.c.} + \mathbf{c}^\dagger_{n,\mathbf{k}_\|}\left[C\mathbf{1} + d(\mathbf{k}_\|)\boldsymbol{\Gamma}_0 + \frac{A}{a}(\boldsymbol{\Gamma}_1\sin k_x a + \boldsymbol{\Gamma}_2\sin k_y a) - \frac{\Delta_{n=1}}{2}\mathbf{m}(t)\cdot\hat{\boldsymbol{\sigma}}\right]\mathbf{c}_{n,\mathbf{k}_\|}\right\} \qquad (2)$$

It yields the correct gap size in the bulk and surface dispersion while reducing to the continuum $\mathbf{k}\cdot\mathbf{p}$ Hamiltonian in the small k limit. Here $\hat{\mathbf{c}} = (\hat{c}_{+\uparrow}, \hat{c}_{+\downarrow}, \hat{c}_{-\uparrow}, \hat{c}_{-\downarrow})^T$ annihilates electron in different orbitals, $d(\mathbf{k})_\| = M - 2B/a^2 + 2B(\cos k_x a + \cos k_y a - 2)/a^2$, $\boldsymbol{\Gamma}_i$ $(i = 0, 1, 2, 3)$ are 4×4 Dirac matrices and $\mathbf{1}$ is the unit matrix of the same size. The numerical values of parameters are chosen as: $M = 0.3$ eV; $A = 0.5$ aeV; and $B = 0.25$ a^2eV. The Fermi energy of the whole device is set at either $E_F = 3.01$ eV or $E_F = 3.35$ eV in order to force it to lie inside (which is topological transport regime) or outside of $\Delta_{\rm surf}^{\rm max}$, and the bottom of the band of the TI slab is shifted by $C = 3.0$ eV.

Figure 3(a) shows the local density of states (LDOS) on the TI surface within the semi-MTJ where the energy-momentum relation bears little resemble to the Dirac cone for strong coupling between the F layer and TI determined by the corresponding inter-layer hopping $\gamma_c = 0.4$ eV (or higher). This is due to flooding of the F|TI interface by evanescent wavefunctions which originate from the F layer and penetrate into the bulk gap of TI while exponentially decaying in space, which is a counterpart of the well-known metal induced gap states in metal-semiconductor Schottky junctions. In other words, for strong F to TI coupling the TI surface state hybridizes with F metallic states so that sharpness of the Dirac cone is lost [18].

To avoid such situation, we assume smaller hopping $\gamma_c = 0.15$ eV where the corresponding LDOS is shown in Fig. 3(b). The weak F to TI coupling can be achieved by growing an ultrathin layer of a conventional band insulator, such as $\mathrm{In_2Se_3}$ with large bandgap and good chemical and structural compatibility with $\mathrm{Bi_2Se_3}$ where sharp heterointerfaces have already been demonstrated by molecular-beam epitaxy growth [19]. This dielectric layer will also affects the value of the proximity induced surface energy gap $\Delta_{\rm surf}$. In addition, Fig. 3 shows that gapped surface state of TI can penetrate into the bulk of TI as evanescent wavefunction decaying over the first three MLs which effectively dopes the bulk.

Although the theory of spin pumping by F|N [13] or F|I [16, 20] interfaces has been developed to a great extent, it is only very recently that strong SOC effects at the interfaces of F layers have been taken into account using scattering approaches [21] or time-dependent NEGF [14, 22]. Since pumped charge and all components of pumped spin current tensor are time-dependent in the presence of SOC [14], NEGF formalism is more advantageous choice because it gives from the outset experimentally measurable current averaged over one period. In contrast, scattering approaches [21] require to compute current at all times (or, in practice, over a discrete time grid) during one period of microwave oscillations and then find its average, which can be difficult in tunneling structures where current amplitude can be several orders of magnitude larger than its average value.

To understand charge pumping in the junction depicted in Fig. 1, we employ our recently derived [14] *exact* multiphoton solution to double-Fourier-transformed NEGFs in the presence of external time periodic fields. Using the operators $\hat{c}_{n\sigma}^\dagger$ ($\hat{c}_{n\sigma}$) which create (annihilate) electron with spin σ on ML n, we can introduce the two fundamental objects [23] of the NEGF formalism—the retarded $G_{nn'}^{r,\sigma\sigma'}(t,t') = -i\Theta(t-t')\langle\{\hat{c}_{n\sigma}(t), \hat{c}_{n'\sigma'}^\dagger(t')\}\rangle$ and the lesser $G_{nn'}^{<,\sigma\sigma'}(t,t') = i\langle\hat{c}_{n'\sigma'}^\dagger(t')\hat{c}_{n\sigma}(t)\rangle$ GF that describe the density of available quantum states and how electrons occupy those states, respectively. Here $\langle\ldots\rangle$ denotes the nonequilibrium statistical average [23].

When the device Hamiltonian depends on time explicitly, as is the case of $\hat{H}^{\rm F} + \hat{H}^{\rm TI}$ above, one has to work with both times. To solve the equation of motion for $\hat{G}_{nn'}^{r,\sigma\sigma'}(t,t')$ and the Keldysh integral equation for $G_{nn'}^{<,\sigma\sigma'}(t,t')$ it is advantageous to switch to a more convenient representation ($\hbar = 1$) [24]

$$\mathbf{G}^{r,<}(t,t') = \int\limits_{-\infty}^{+\infty} \frac{dE}{2\pi} \int\limits_{-\infty}^{+\infty} \frac{E'}{2\pi}\, e^{-iEt+iE't'}\,\mathbf{G}^{r,<}(E,E'). \quad (3)$$

Due to the Floquet theorem, the double-time Fourier transformed retarded GF, $\hat{G}^r(E,E')$, must take the form $\mathbf{G}^r(E,E') = \mathbf{G}^r(E,E+N\omega) = \mathbf{G}_N^r(E)$. The coupling of energies E and $E+N\omega$, where N is integer, signifies how multiphoton processes assist the generation of pumped current. Since the junction in Fig. 1 is translationally invariant in the transverse direction, we additionally perform spatial Fourier transform in the yz-plane, so that multiphoton retarded GF depends on $\mathbf{k}_\|$.

Assuming absence of electron interactions with phonons, magnons, or other electrons, solving $[E\check{\mathbf{1}} + \check{\mathbf{\Omega}} - \check{\mathbf{H}}_{\mathbf{k}_\|} - \check{\mathbf{\Sigma}}_{\mathbf{k}_\|}^r(E+\check{\mathbf{\Omega}})]\check{\mathbf{G}}_{\mathbf{k}_\|}^r(E) = \hat{\mathbf{1}}$ for the multiphoton retarded GF is sufficient to express the time-averaged total pumped charge current in N lead $p = L, R$ as:

$$\begin{aligned} I_p &= \frac{e}{2N_{\rm ph}} \int d\mathbf{k}_\|\, {\rm Tr}\,\{\check{\mathbf{\Gamma}}_{p,\mathbf{k}_\|}[\check{\mathbf{\Omega}}, \check{\mathbf{G}}_{\mathbf{k}_\|}^r(E_F)\check{\mathbf{\Gamma}}_{\mathbf{k}_\|}(E_F)]\}, \\ & [\check{\mathbf{\Omega}}, \check{\mathbf{G}}_{\mathbf{k}_\|}^r(E_F)\check{\mathbf{\Gamma}}_{\mathbf{k}_\|}(E_F)] = \check{\mathbf{\Omega}}\check{\mathbf{G}}_{\mathbf{k}_\|}^r(E_F)\check{\mathbf{\Gamma}}_{\mathbf{k}_\|}(E_F) \\ & -\check{\mathbf{G}}_{\mathbf{k}_\|}^r(E_F)\check{\mathbf{\Gamma}}_{\mathbf{k}_\|}(E_F)\check{\mathbf{\Omega}}, \end{aligned} \quad (4)$$

where adiabatic limit $\omega \ll E_F$ satisfied by microwaves is taken into account. The symbol $\check{\mathbf{A}}$ means that matrix acts in the Hilbert space $\mathcal{H}_{\rm el} \otimes \mathcal{H}_{\rm ph}$, where the dimension of the Hilbert space of photons $\mathcal{H}_{\rm ph}$ is infinite [14] and the dimension of $\mathcal{H}_{\rm el}$ is equal to the number of F and TI MLs, $d_{\rm F} + d_{\rm TI}$. The unit matrix in the Hilbert space of a single electron $\mathcal{H}_{\rm el}$ is $\mathbf{1}$, so that the unit matrix in $\mathcal{H}_{\rm el} \otimes \mathcal{H}_{\rm ph}$ is denoted by $\check{\mathbf{1}}$. Here $\check{\mathbf{\Omega}} = {\rm diag}\,(\cdots, -2\omega\mathbf{1}, -\omega\mathbf{1}, 0, \omega\mathbf{1}, -2\omega\mathbf{1}, \cdots)$ is the diagonal matrix, $\check{\mathbf{\Gamma}} = \sum_p \check{\mathbf{\Gamma}}_p$ is the level broadening matrix due to the coupling of the F|TI bilayer to N leads. Since the trace in the integrand, ${\rm Tr} \equiv {\rm Tr}_{\rm el}{\rm Tr}_{\rm ph}$, is summing over contributions from different photon exchange processes, the denominator includes $2N_{\rm ph}$ to avoid double counting. Note that the part of the trace operating in $\mathcal{H}_{\rm ph}$ space ensures the current conservation in our solution to NEGF equations. We find that $N_{\rm ph} = 10$ is sufficient to obtain asymptotic value of pumped charge current. The pumped charge current is then translated into the *dc pumping voltage* in an open circuit via $V_{\rm pump} = I_p/G(\theta)$ which is the quantity measured in recent experiments on F|I|N semi-MTJs driven by microwaves [15].

Note added. During the preparation of this manuscript we noticed Ref. [25] where charge pumping was found for the same device as in Fig. 1 but with current flowing on the surface of TI (i.e., within the yz-plane) rather than perpendicularly through such interface. Another major difference is that TFT treatment in Ref. [25] requires perfectly insulating bulk, while our vertical junction setup can operate even if there are excessive bulk charge carries in the interior of the TI slab.

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